United States Patent [19]

Cha

[54] **PROGRAM CIRCUIT**

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[58] **Field of Search** 365/189.07, 201, 365/185.22

[56]   **References Cited**

U.S. PATENT DOCUMENTS

4,811,294	3/1989	Kobayashi et al.	.... 365/189.07
5,299,162	3/1994	Kim et al.	.... 365/201
5,629,890	5/1997	Engh	.... 365/189.07

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[57]   **ABSTRACT**

The program circuit according to the present invention can apply a program voltage to the only memory cells which are not programmed during a re-programming operation, thus, the present invention can be prevent a lowering of reliability of the memory cell due to a continued supply of a program bias voltage.

4 Claims, 1 Drawing Sheet